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Supplementary Material

Schottky Barrier Height and Image Force Lowering in Monolayer MoS_2 Field Effect Transistors

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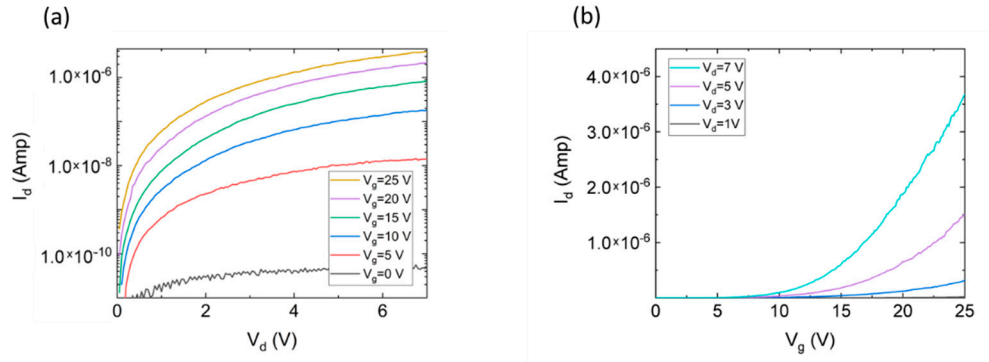


Figure S1. (**a**) $I_d(V_d)$ characteristics. (**b**) $I_d(V_g)$ characteristics.

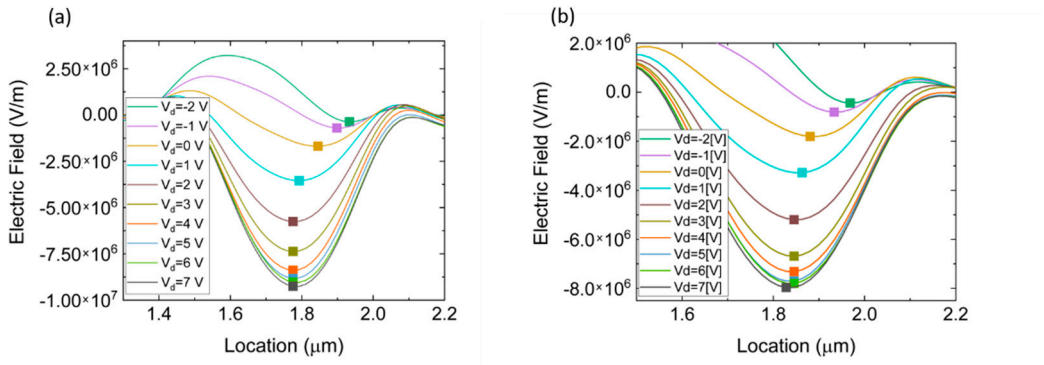


Figure S2. (**a**) and (**b**) Electric field distribution at the gold/MoS_2 interface periphery of the source contact, for both $V_{Back-gate}$ = 0 V and $V_{Back-gate}$ = −3 V, respectively. The electric fields were calculated as the first derivation of the CPD distribution presented in Figure 2a and 2c of the manuscript, measured by the KPFM.

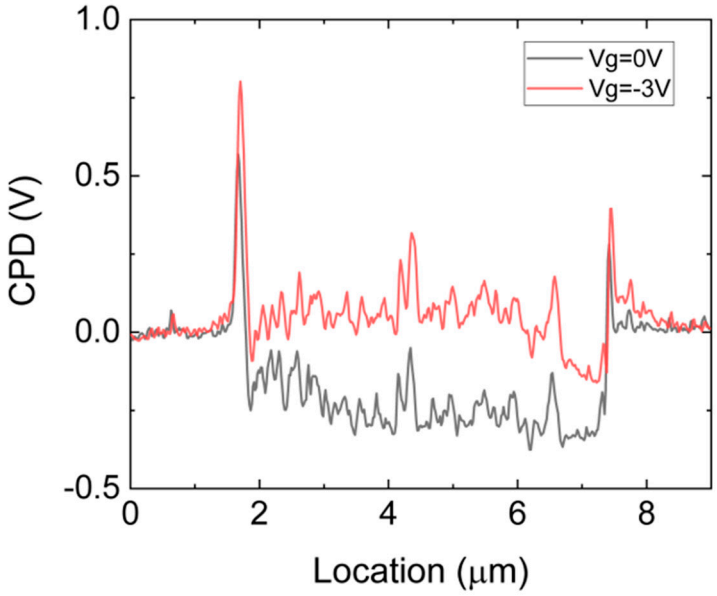


Figure S3. CPD profile of both V_g = 0 V and V_g = −3 V at V_d = V_s = 0 V presenting separations of 0.3 eV are presented.

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